

Jinbiao Liu

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/6726587/publications.pdf>

Version: 2024-02-01

10
papers

352
citations

1307594

7
h-index

1474206

9
g-index

10
all docs

10
docs citations

10
times ranked

361
citing authors

#	ARTICLE	IF	CITATIONS
1	State of the Art and Future Perspectives in Advanced CMOS Technology. <i>Nanomaterials</i> , 2020, 10, 1555.	4.1	115
2	Miniaturization of CMOS. <i>Micromachines</i> , 2019, 10, 293.	2.9	81
3	The Challenges of Advanced CMOS Process from 2D to 3D. <i>Applied Sciences (Switzerland)</i> , 2017, 7, 1047.	2.5	53
4	Review of Si-Based GeSn CVD Growth and Optoelectronic Applications. <i>Nanomaterials</i> , 2021, 11, 2556.	4.1	42
5	Integration of Highly Strained SiGe in Source and Drain with HK and MG for 22Ånm Bulk PMOS Transistors. <i>Nanoscale Research Letters</i> , 2017, 12, 123.	5.7	22
6	Defect engineering for shallow n ⁺ -type junctions in germanium: Facts and fiction. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016, 213, 2799-2808.	1.8	18
7	pMOSFETs Featuring ALD W Filling Metal Using SiH ₄ and B ₂ H ₆ Precursors in 22 nm Node CMOS Technology. <i>Nanoscale Research Letters</i> , 2017, 12, 306.	5.7	13
8	Study of n-type doping in germanium by temperature based PF ⁺ implantation. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 161-166.	2.2	4
9	Improving Driving Current with High-Efficiency Landing Pads Technique for Reduced Parasitic Resistance in Gate-All-Around Si Nanosheet Devices. <i>ECS Journal of Solid State Science and Technology</i> , 2022, 11, 035010.	1.8	4
10	Low-Temperature (â‰‰500 Å°C) Complementary Schottky Source/Drain FinFETs for 3D Sequential Integration. <i>Nanomaterials</i> , 2022, 12, 1218.	4.1	0